

NANOBITM CMP slurry for SiC Epi-Ready wafer

スクラッチ、基板ダメージ、加工速度、洗浄性を解決します

Solves Scrach, Sub surface damage, processing speed, and cleanability issues



pH	8~9
Sub surface damage	Very low
Removal rate	7 $\mu\text{m}/\text{min}$ ※
Cleanability	Excellent

※実際の値はお客様の使用環境によります。
(研磨条件に依存します)

※Actual value in customers
(depends on polishing conditions)

Scratch Free & Speedy Process

低硬度の粒子が高品質な研磨を実現します。

Low-hardness particles realize high-quality polishing.

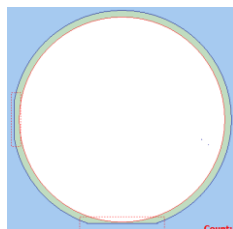
Grinding wafer



Epi-ready wafer

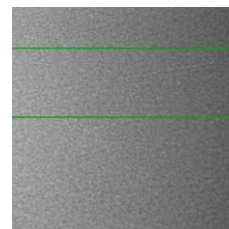
Speedy polishing
by NANOBITM

Scratch free



SICA 6X
(After CMP)

Low sub surface density



MEM

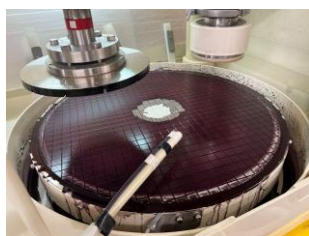
(Mirror Projection Electron Microscopy)
By Hitachi High-Tech

Easy Cleaning

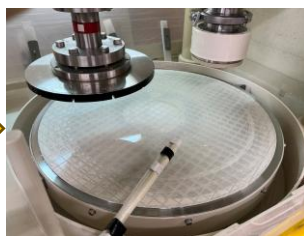
MnO₂粒子は酸に溶解します。

Dissolve MnO₂ particles by Acid Washing.

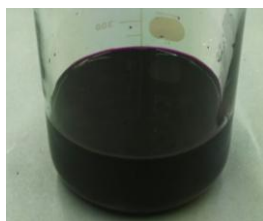
- ✓ SiO₂、Al₂O₃より
洗浄が速い
- ✓ Cleaning speedy
than SiO₂, Al₂O₃



Acid
washing



- ✓ MnO₂粒子は残ら
ない
- ✓ No MnO₂ particles
remain



Acid
washing



	Units of 1e10 atoms/cm ² Measured by TREX 610-T
Mn	0.3
K	< 2 (D.L.)
Na	< 50 (D.L.)
Mg	< 30 (D.L.)
Al	< 40 (D.L.)

※D.L. ⇒ Detection limit

秉持探索精神，
融汇多样技术，
让地球绽放笑容。

